

60V, 198A, 1.9mΩ N-channel Power SGT MOSFET
JMSH0602PEQ
Features

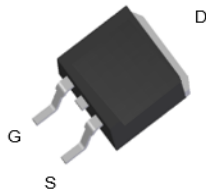
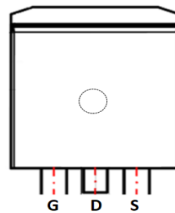
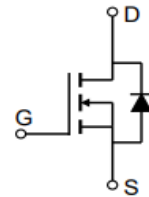
- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant
- AEC-Q101 Qualified

Applications

- Load Switch
- PWM Application
- General Automotive Application

Product Summary

Parameters	Value	Unit
V_{DSS}	60	V
$V_{GS(th_Typ)}$	2.8	V
$I_D(@V_{GS}=10V)$	198	A
$R_{DS(ON_Typ)}(@V_{GS}=10V)$	1.9	mΩ


TO-263 -3L

Pin Assignment

Schematic Diagram
Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0602PEQ-13	SH0602PQ	1	Tape&Reel	TO-263-3L	800	4000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	198
		$T_C = 100^\circ\text{C}$	140
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	497	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	188
		$T_C = 100^\circ\text{C}$	94
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	41	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.8	

**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1.9	2.8	3.6	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$	-	1.9	2.5	m Ω
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	2.7	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 30\text{V}$, $f = 1\text{MHz}$	3267	4574	6175	pF
C_{oss}	Output Capacitance		1664	2330	3146	pF
C_{riss}	Reverse Transfer Capacitance		73	102	137	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 30\text{V}$, $I_D = 20\text{A}$	50	70	94	nC
Q_{gs}	Gate Source Charge		15	21	29	nC
Q_{gd}	Gate Drain("Miller") Charge		12	17	23	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$, $V_{DD} = 30\text{V}$ $I_D = 20\text{A}$, $R_{GEN} = 3\Omega$	-	17.1	-	ns
t_r	Turn-On Rise Time		-	32	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	46	-	ns
t_f	Turn-Off Fall Time		-	26	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	198	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	793	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 20\text{A}$	-		1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$	47	65	88	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	87	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 30\text{V}$, $V_G = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 18.2\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

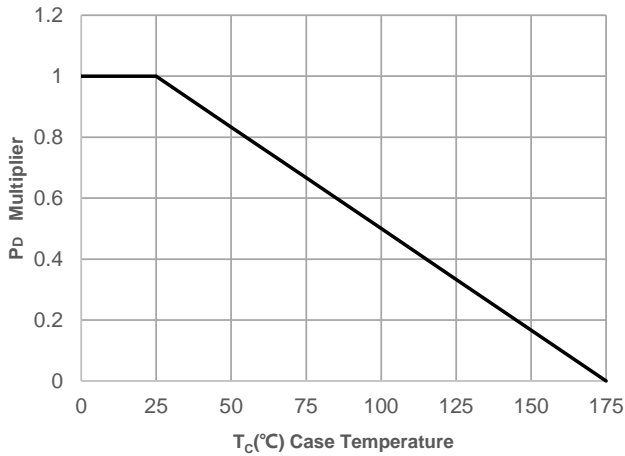


Figure 2: Current De-rating

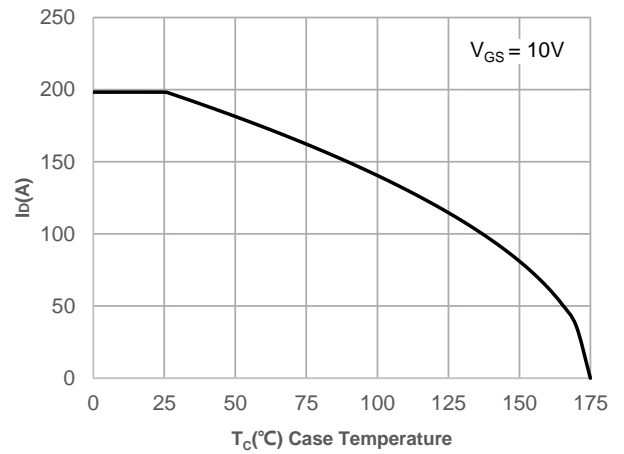


Figure 3: Normalized Maximum Transient Thermal Impedance

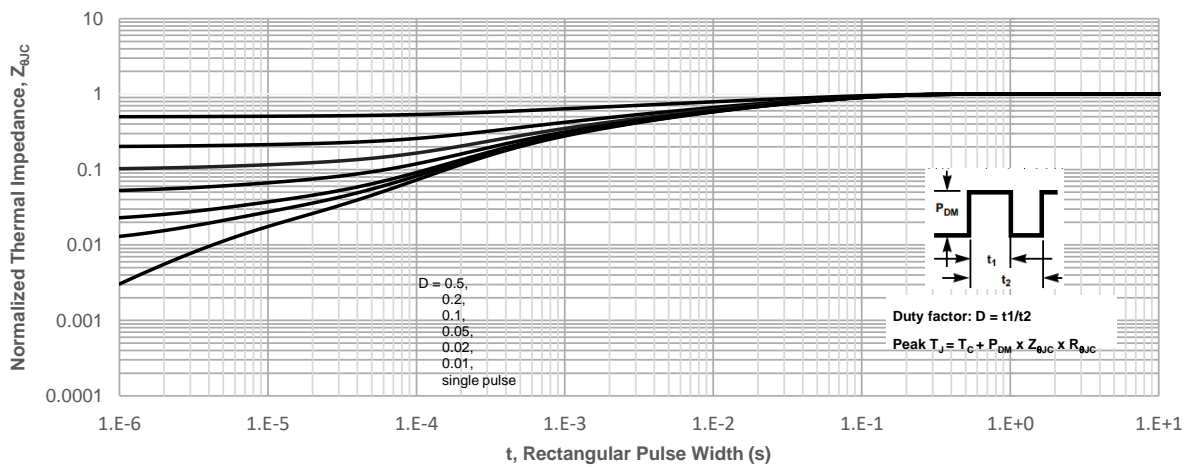
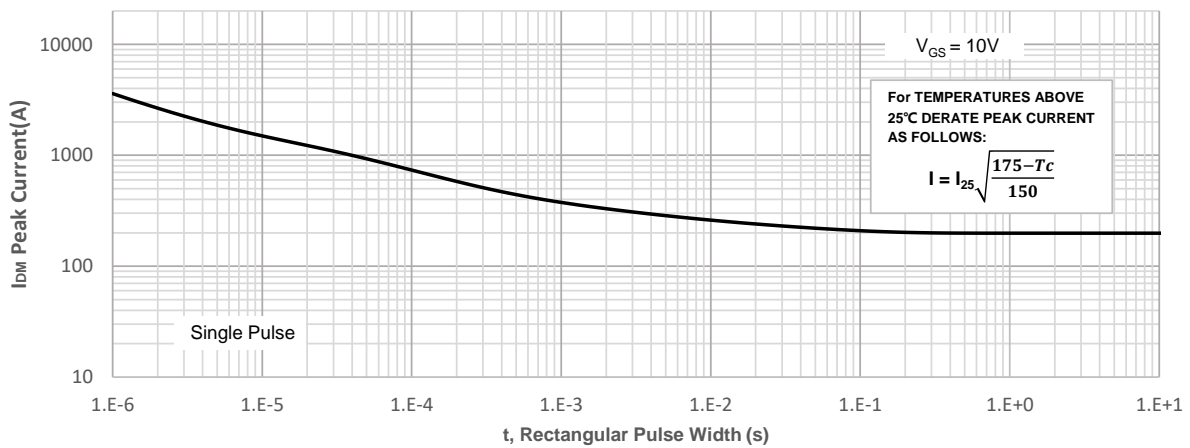


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

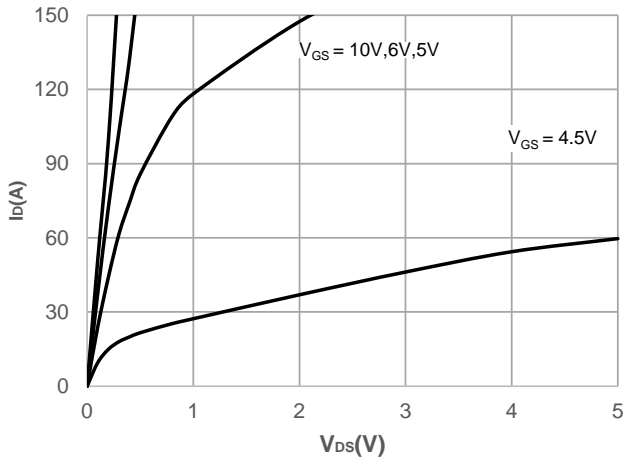


Figure 6: Typical Transfer Characteristics

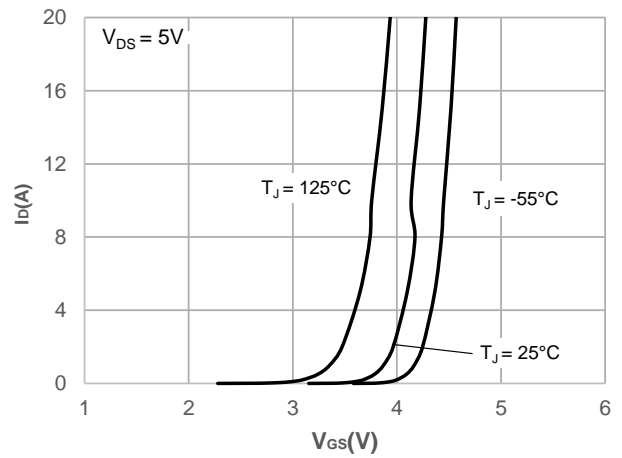


Figure 7: On-resistance vs. Drain Current

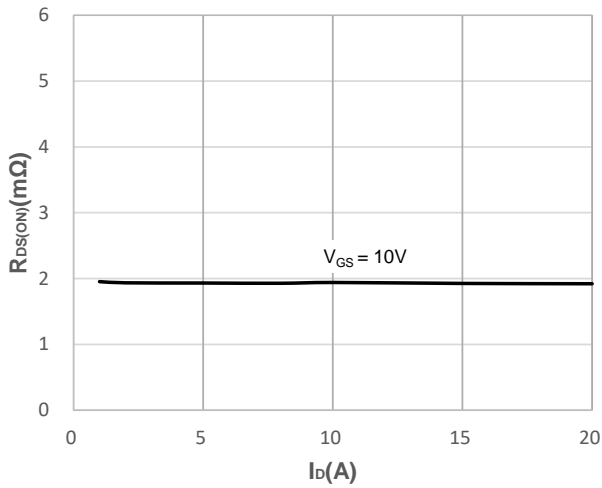


Figure 8: Body Diode Characteristics

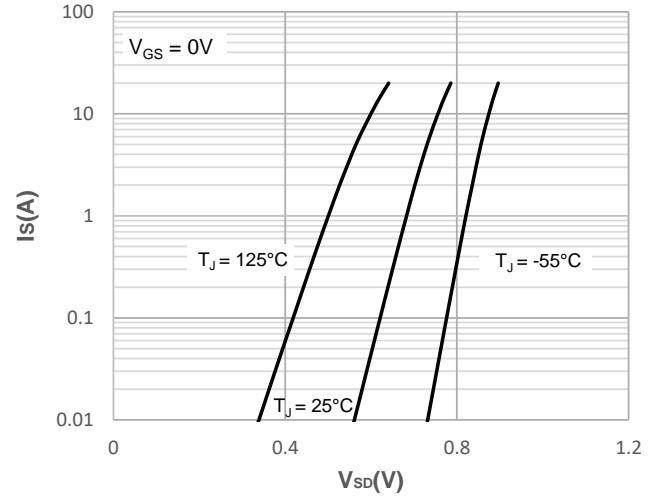


Figure 9: Gate Charge Characteristics

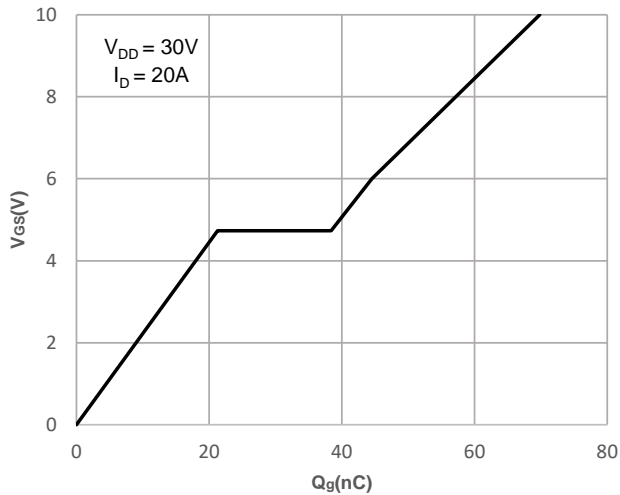
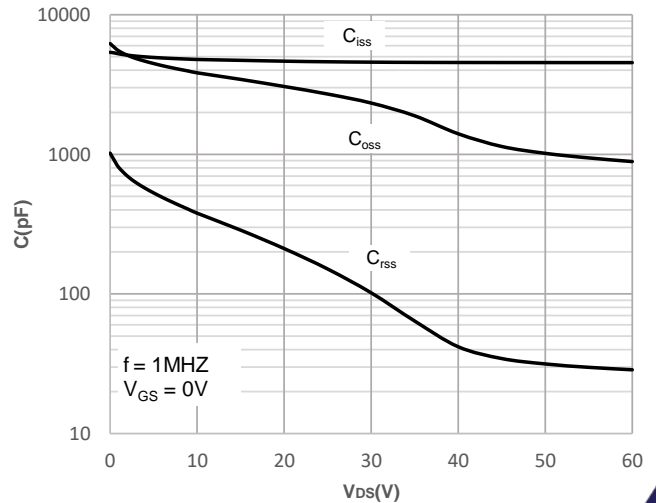


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

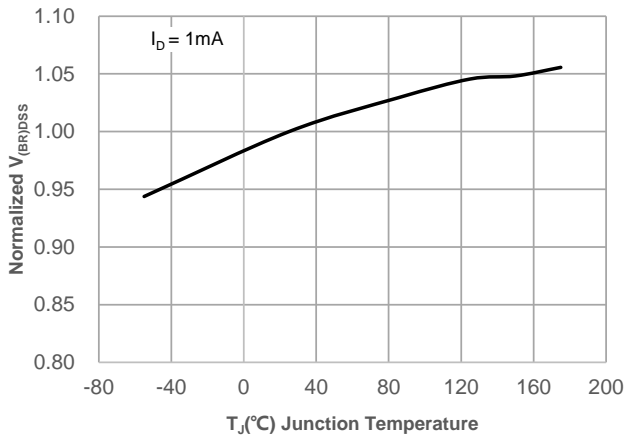


Figure 12: Normalized on Resistance vs. Junction Temperature

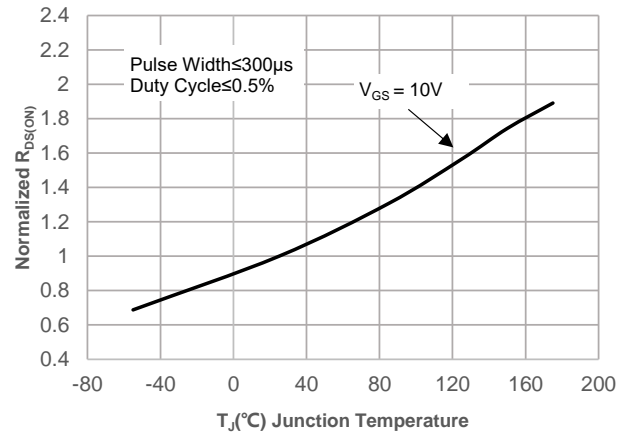


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

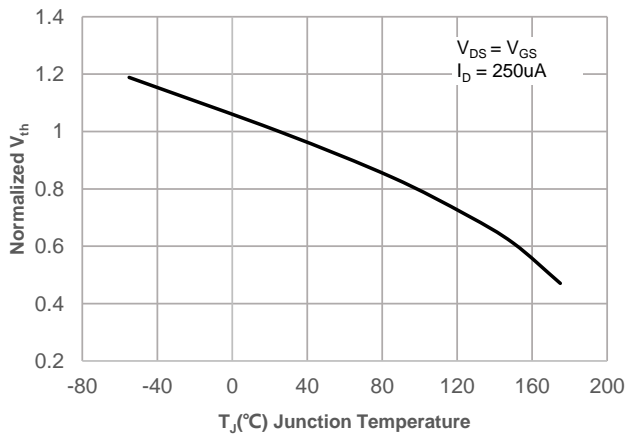


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

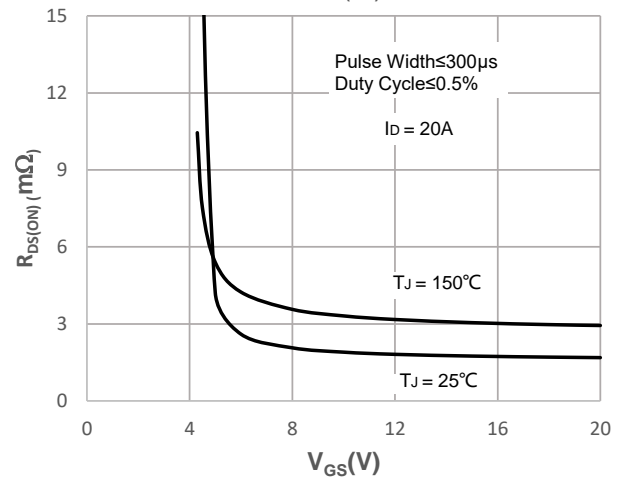
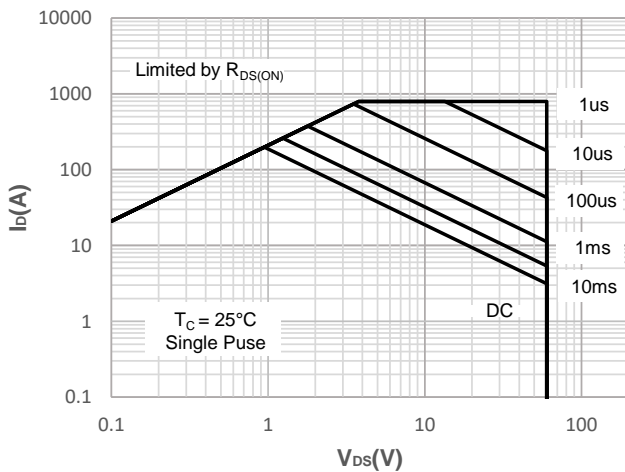


Figure 15: Maximum Safe Operating Area



Test Circuit

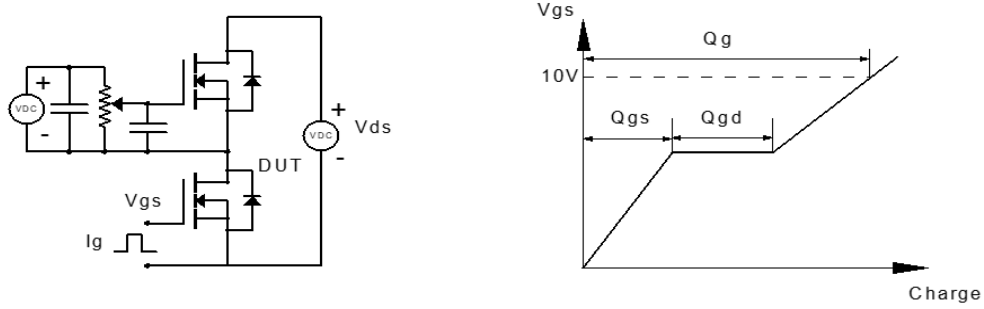


Figure 1: Gate Charge Test Circuit & Waveform

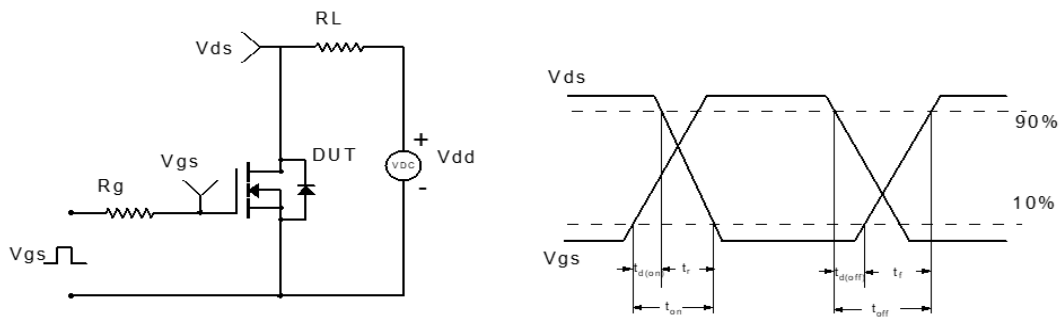


Figure 2: Resistive Switching Test Circuit & Waveform



Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

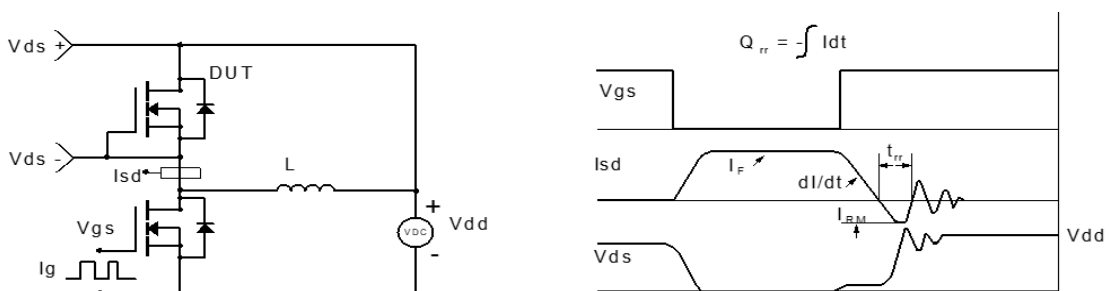
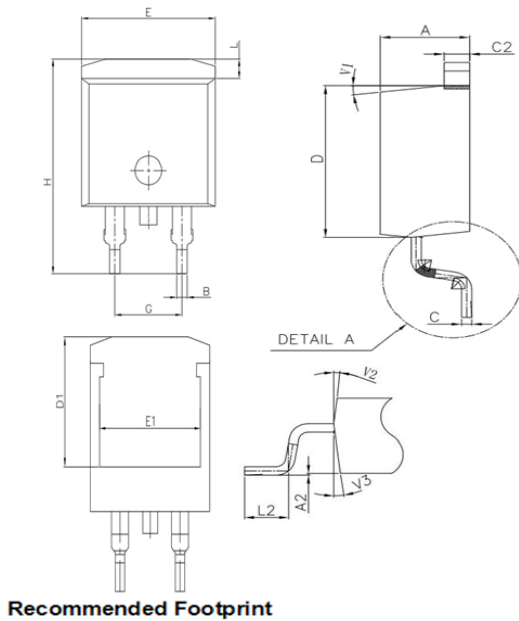


Figure 4: Diode Recovery Test Circuit & Waveform

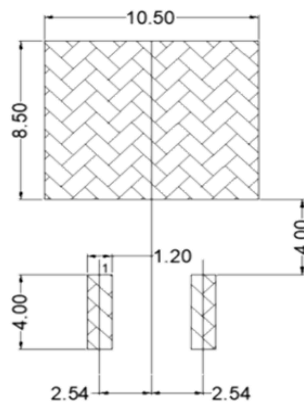


Package Mechanical Data(TO-263 -3L)

Package Outline



SYMBOL	DIMENSIONS		
	MIN	NOM	MAX
A	4.3	4.55	4.7
A2	0		0.15
B	0.75	0.8	0.85
C	0.38	0.46	0.55
C2	1.25	1.3	1.35
D	8.9	9.3	9.6
D1	7.4	7.65	7.9
E	9.9	10.05	10.21
E1	8.3	8.6	8.9
G	5.03	5.08	5.13
H	14.7	15	15.8
L2	2.2	2.35	2.5



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co.,Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information.

is a registered trademark of Jiangsu JieJie Microelectronics Co.,Ltd.